ELECTRONICS, INC.
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NTE553
Schottky Barrier Diode

Description:

The NTE553 is a silicon schottky barrier diode in a DO35 style package for use in UHF and VHF switching applications.

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Reverse Voltage, V_R . . . . . –35V
Forward Current, I_F 100mA
Power Dissipation, P_D 150mW
Operating Temperature Range, T_{opr} . . . . . –20° to + 60°C
Storage Temperature range, T_{stg} . . . . . –45° to + 125°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R = –10μA	–35	–	–	V
Reverse Leakage Current	I_R	V_R = –25V	–	–	–0.1	μA
Forward Voltage	V_F	I_F = 10mA	–	–	1.0	V
Diode Capacitance	C_T	V_R = –6V, f = 1MH$_Z$	–	–	1.2	pf
Series Resistance	R_S	I_F = 2mA, f = 100MH$_Z$	–	–	1.2	Ω
Series Inductance	L_S	f = 250MH$_Z$	–	3	–	nH